

/ Descriptions

TO-220F PNP Silicon PNP transistor in a TO-220F Plastic Package.

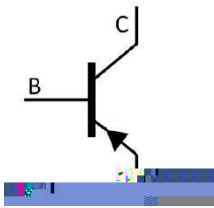
/ Features

Good linearity of h_{FE} , complementary to KTC4369.

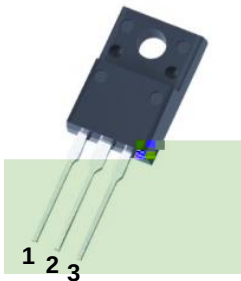
/ Applications

General purpose amplifier.

/ Equivalent Circuit



/ Pinning



PIN1	Base	PIN 2	Collector	PIN 3	Emitter
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/ h_{FE} Classifications & Marking

h _{FE} Classifications Symbol	O	Y
h _{FE} Range	70 140	120 240

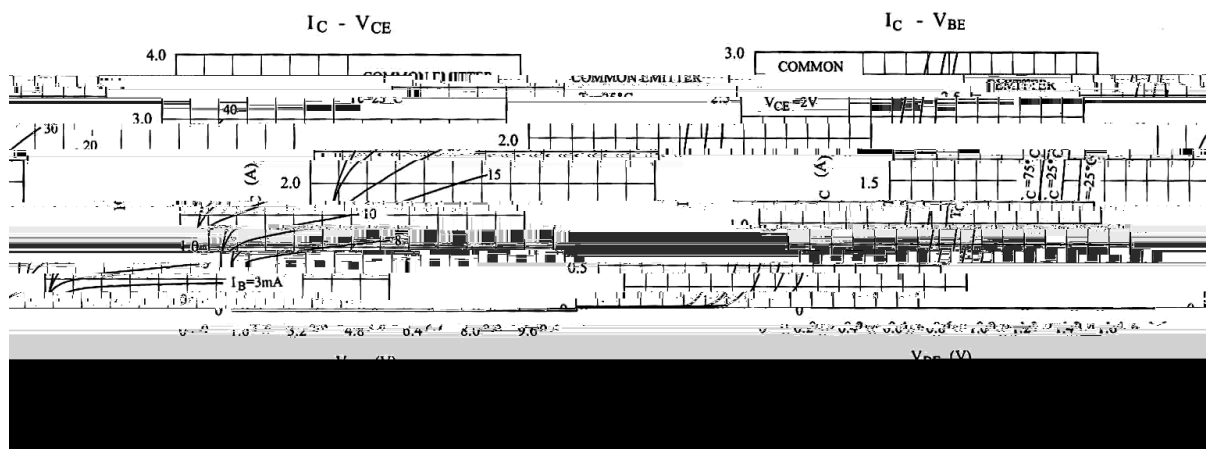
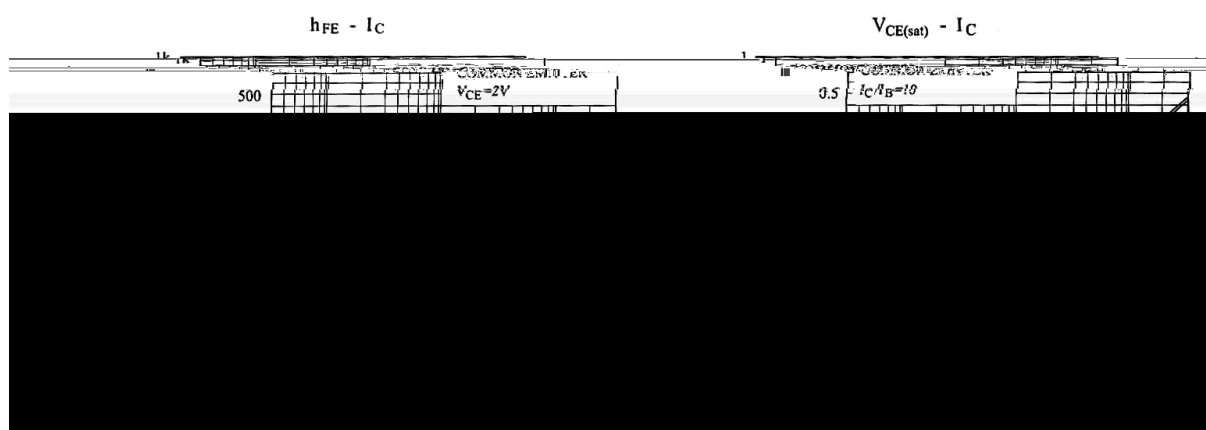
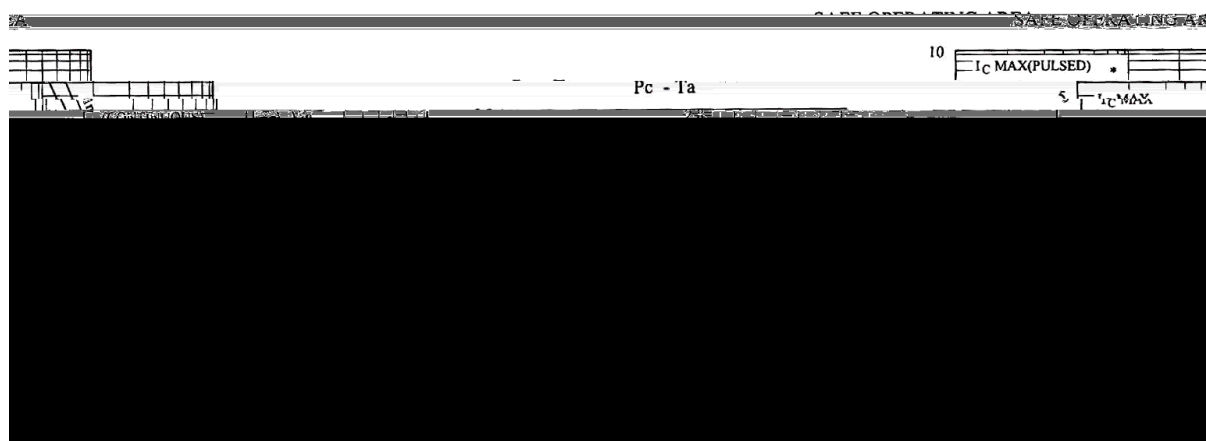
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-3.0	A
Base Current	I_B	-0.3	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C(T_c=25)$	15	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

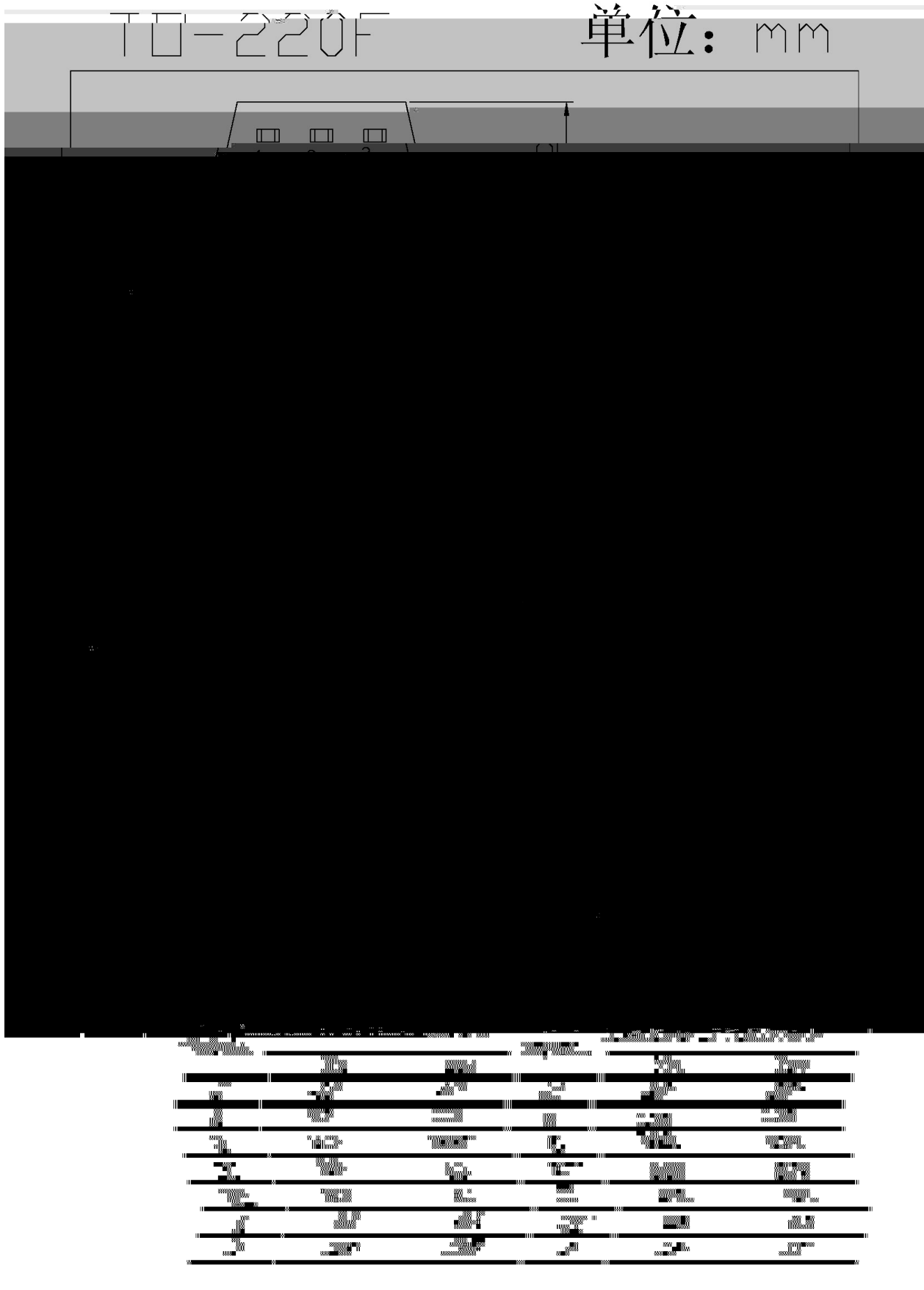
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-10mA$ $I_B=0$	-30			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-20V$ $I_E=0$			-1.0	A
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-1.0	A
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-2.0V$ $I_C=-0.5A$	70		240	
	$h_{FE(2)}$	$V_{CE}=-2.0V$ $I_C=-2.5A$	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-2.0A$ $I_B=-0.2A$		-0.3	-0.8	V
Collector to Emitter Voltage	V_{BE}	$V_{CE}=-2.0V$ $I_C=-0.5A$		-0.75	-1.0	V
Transition Frequency	f_T	$V_{CE}=-2.0V$ $I_C=-0.5A$		100		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V$ $I_E=0$ $f=1.0MHz$		40		pF

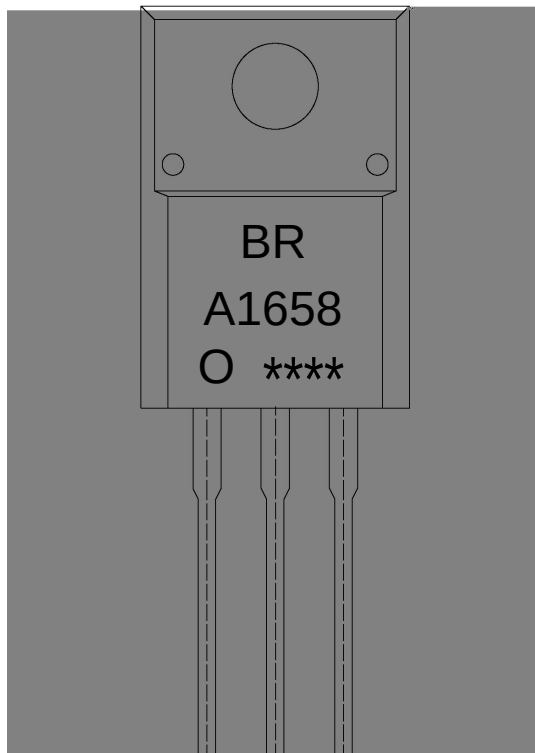
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

A1658

O: h_{FE}

Note:

BR: Company Code.

A1658: Product Type.

O: h_{FE} Classifications Symbol.

****: Lot No. Code, code change with Lot No.

